# **20V N-CHANNEL ENHANCEMENT MODE MOSFET**

# **SUMMARY**

 $V_{(BR)DSS} = 20V : R_{DS}(on) = 0.06\Omega; I_D = 4.1A$ 

# **DESCRIPTION**

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



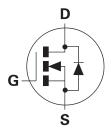
**SOT23** 

# **FEATURES**

- Low on-resistance
- Fast switching speed
- Low threshold
- · Low gate drive
- SOT23 package

# **APPLICATIONS**

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

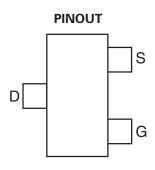


# **ORDERING INFORMATION**

| DEVICE      | REEL | TAPE  | QUANTITY   |  |
|-------------|------|-------|------------|--|
|             | SIZE | WIDTH | PER REEL   |  |
| ZXMN2A14FTA | 7″   | 8mm   | 3000 units |  |

# **DEVICE MARKING**

• 214





# **ABSOLUTE MAXIMUM RATINGS**

| PARAMETER   | SYMBOL                            | LIMIT       | UNIT  |
|---|-----------------------------------|-------------|-------|
| Drain-Source Voltage  | V <sub>DSS</sub>                  | 20          | V     |
| Gate-Source Voltage   | V <sub>GS</sub>                   | ±12         | V     |
| Continuous Drain Current @ V <sub>GS</sub> =4.5V; T <sub>A</sub> =25°C <sup>(b)</sup> | I <sub>D</sub>                    | 4.1         | A     |
| @ V <sub>GS</sub> =4.5V; T <sub>A</sub> =70°C <sup>(b)</sup>                          |                                   | 3.3         | Α     |
| @ V <sub>GS</sub> =4.5V; T <sub>A</sub> =25°C <sup>(a)</sup>                          |                                   | 3.4         | A     |
| Pulsed Drain Current (c)  | I <sub>DM</sub>                   | 19          | А     |
| Continuous Source Current (Body Diode) (b)  | I <sub>S</sub>                    | 1.7         | А     |
| Pulsed Source Current (Body Diode) (c)  | I <sub>SM</sub>                   | 19          | А     |
| Power Dissipation at T <sub>A</sub> =25°C <sup>(a)</sup>                              | P <sub>D</sub>                    | 1           | W     |
| Linear Derating Factor  |                                   | 8           | mW/°C |
| Power Dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>                              | P <sub>D</sub>                    | 1.5         | W     |
| Linear Derating Factor  |                                   | 12          | mW/°C |
| Operating and Storage Temperature Range   | T <sub>j</sub> , T <sub>stg</sub> | -55 to +150 | °C    |

# THERMAL RESISTANCE

| PARAMETER                          | SYMBOL          | VALUE | UNIT |
|------------------------------------|-----------------|-------|------|
| Junction to Ambient <sup>(a)</sup> | $R_{\Theta JA}$ | 125   | °C/W |
| Junction to Ambient <sup>(b)</sup> | $R_{\Theta JA}$ | 82    | °C/W |

# NOTES

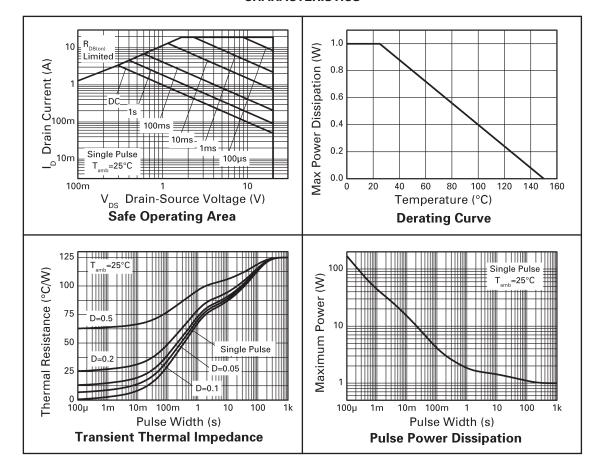
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.



<sup>(</sup>b) For a device surface mounted on FR4 PCB measured at  $t \le 5$  sec.

<sup>(</sup>c) Repetitive rating - 25mm x 25mm FR4 PCB, D=0.02, pulse width 300 µs - pulse width limited by maximum junction temperature.

# **CHARACTERISTICS**





# **ELECTRICAL CHARACTERISTICS** (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

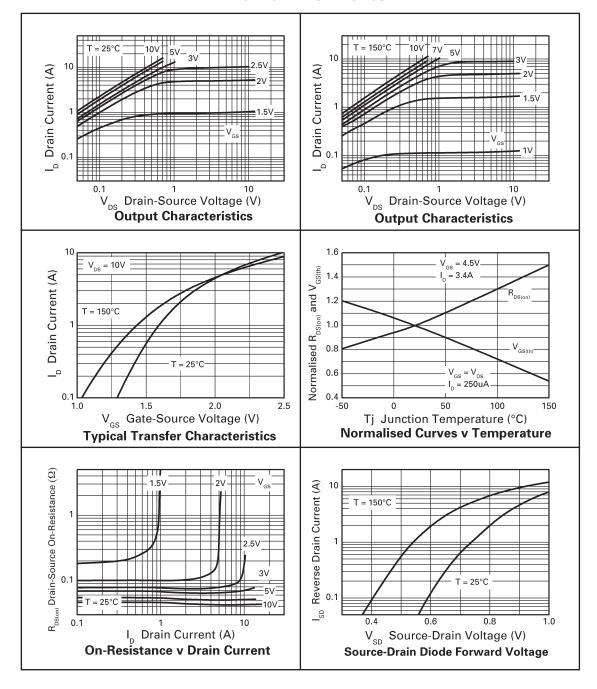
| PARAMETER                        | SYMBOL               | MIN. | TYP. | MAX.  | UNIT | CONDITIONS   |  |
|----------------------------------|----------------------|------|------|-------|------|--|--|
| STATIC                           | '                    | 1    |      |       |      |  |  |
| Drain-Source Breakdown Voltage   | V <sub>(BR)DSS</sub> | 20   |      |       | V    | I <sub>D</sub> =250μA, V <sub>GS</sub> =0V               |  |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>     |      |      | 1     | μΑ   | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V                |  |
| Gate-Body Leakage                | I <sub>GSS</sub>     |      |      | 100   | nA   | $V_{GS} = \pm 12V, V_{DS} = 0V$                          |  |
| Gate-Source Threshold Voltage    | V <sub>GS(th)</sub>  | 0.7  |      |       | V    | I <sub>D</sub> =250μA, V <sub>DS</sub> = V <sub>GS</sub> |  |
| Static Drain-Source On-State     | R <sub>DS(on)</sub>  |      |      | 0.060 | Ω    | V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.4A              |  |
| Resistance <sup>(1)</sup>        |                      |      |      | 0.110 | Ω    | V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.5A              |  |
| Forward Transconductance (1) (3) | g <sub>fs</sub>      |      | 9.4  |       | S    | V <sub>DS</sub> =10V,I <sub>D</sub> =3.4A                |  |
| DYNAMIC (3)                      |                      | •    | •    |       |      | •  |  |
| Input Capacitance                | C <sub>iss</sub>     |      | 544  |       | pF   |  |  |
| Output Capacitance               | C <sub>oss</sub>     |      | 132  |       | pF   | V <sub>DS</sub> = 10V, V <sub>GS</sub> =0V,              |  |
| Reverse Transfer Capacitance     | C <sub>rss</sub>     |      | 85   |       | pF   | f=1MHz   |  |
| SWITCHING <sup>(2) (3)</sup>     |                      | •    |      |       | •    |  |  |
| Turn-On Delay Time               | t <sub>d(on)</sub>   |      | 4.0  |       | ns   |  |  |
| Rise Time                        | t <sub>r</sub>       |      | 5.3  |       | ns   | $V_{DD} = 10V, V_{GS} = 4.5V$                            |  |
| Turn-Off Delay Time              | t <sub>d(off)</sub>  |      | 16.6 |       | ns   | I <sub>D</sub> = 1A                                      |  |
| Fall Time                        | t <sub>f</sub>       |      | 9.5  |       | ns   | $R_{G} \cong 6.0\Omega$                                  |  |
| Total Gate Charge                | Qg                   |      | 6.6  |       | nC   |  |  |
| Gate-Source Charge               | Q <sub>gs</sub>      |      | 1.2  |       | nC   | $V_{DS} = 10V, V_{GS} = 4.5V,$                           |  |
| Gate-Drain Charge                | Q <sub>gd</sub>      |      | 2.1  |       | nC   | I <sub>D</sub> =3.4A                                     |  |
| SOURCE-DRAIN DIODE               | 1                    | 1    |      |       |      | 1  |  |
| Diode Forward Voltage (1)        | V <sub>SD</sub>      |      | 0.85 | 0.95  | V    | T <sub>J</sub> =25°C, I <sub>S</sub> =(3.3)A,            |  |
|                                  |                      |      |      |       |      | V <sub>GS</sub> =0V                                      |  |
| Reverse Recovery Time (3)        | t <sub>rr</sub>      |      | 11.4 |       | ns   | T <sub>J</sub> =25°C, I <sub>F</sub> =(1.7)A,            |  |
| Reverse Recovery Charge (3)      | Q <sub>rr</sub>      |      | 4.6  |       | nC   | di/dt= 100A/μs   |  |

# **NOTES**

- (1) Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq\!2\%.$
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.



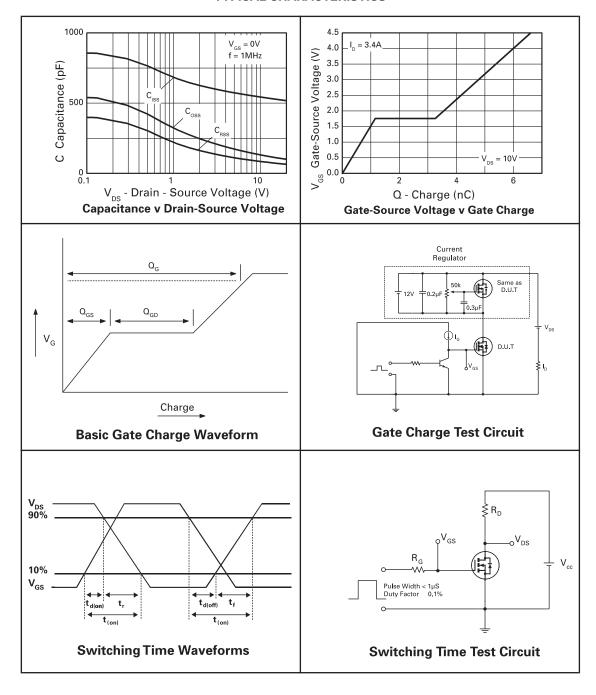
# **TYPICAL CHARACTERISTICS**







# **TYPICAL CHARACTERISTICS**





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## Datasheet status key:

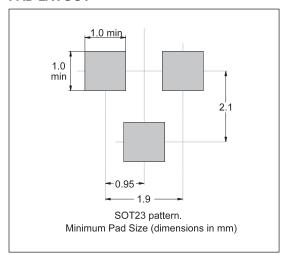
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# **PACKAGE OUTLINE**

# 3 EADS D

# **PAD LAYOUT**



Controlling dimensions are in millimetres. Approximate conversions are given in inches

# **PACKAGE DIMENSIONS**

|     | MILLIMETRES |      | INCHES |        |     | MILLIMETRES |      | INCHES     |        |
|-----|-------------|------|--------|--------|-----|-------------|------|------------|--------|
| DIM | MIN         | MAX  | MIN    | MAX    | DIM | MIN         | MAX  | MIN        | MAX    |
| Α   | 2.67        | 3.05 | 0.105  | 0.120  | Н   | 0.33        | 0.51 | 0.013      | 0.020  |
| В   | 1.20        | 1.40 | 0.047  | 0.055  | K   | 0.01        | 0.10 | 0.0004     | 0.004  |
| С   | _           | 1.10 | _      | 0.043  | L   | 2.10        | 2.50 | 0.083      | 0.0985 |
| D   | 0.37        | 0.53 | 0.015  | 0.021  | М   | 0.45        | 0.64 | 0.018      | 0.025  |
| F   | 0.085       | 0.15 | 0.0034 | 0.0059 | N   | 0.95 NOM    |      | 0.0375 NOM |        |
| G   | 1.90 NOM    |      | 0.075  | NOM    | θ   | 10° TYP 1   |      | 10°        | TYP    |

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